

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently amended) A semiconductor manufacturing device comprising:
having

a mechanical drive part that ~~which~~ is moveable ~~moved~~ in a vacuum device while
holding a substrate ~~comprising,~~

~~at least one~~ a discharge port for introducing inert gas into said vacuum device, and

a flow rate control part for controlling the inert gas that ~~which~~ is discharged ~~discharge~~
into said vacuum device from said discharge port at a constant flow rate.

Claim 2. (Currently amended) A semiconductor manufacturing device comprising:

a mechanical drive part that is moveable in a vacuum device while holding a
substrate,

a discharge port for introducing inert gas into said vacuum device;

a flow rate control part for controlling the inert gas that is discharged into said
vacuum device from said discharge port at a constant flow rate; and

~~The semiconductor manufacturing device as claimed in claim 1, further comprising~~
an inspection processing part for inspecting said substrate.

Claim 3. (Previously presented) The semiconductor manufacturing device as claimed in
claim 1, further comprising an exposure processing part for exposing said substrate.

Claim 4. (Previously presented) The semiconductor manufacturing device as claimed in
claim 1, wherein said discharge port is disposed at a position in the vicinity of the substrate

held by said mechanical drive part where it does not make contact with the substrate.

Claim 5. (Previously presented) The semiconductor manufacturing device as claimed in claim 1, wherein said mechanical drive part is located between said discharge port and a vacuum exhaust port in said vacuum device.

Claim 6. (Currently amended) A semiconductor manufacturing device comprising:
a mechanical drive part that is moveable in a vacuum device while holding a
substrate,

a discharge port for introducing inert gas into said vacuum device;
a flow rate control part for controlling the inert gas that is discharged into said
vacuum device from said discharge port at a constant flow rate; and ~~The semiconductor~~
~~manufacturing device as claimed in claim 1,~~ wherein

the total evacuation rate of the vacuum pump connected to said vacuum device is more than 300L/s and less than 5,000L/s,

the degree of vacuum within said vacuum device is higher than 133×10^{-7} kPa and lower than 133×10^{-4} kPa, and

the flow rate of said inert gas is more than 0.5cm³/min and less than 20cm³/min.

Claim 7. (New) A semiconductor manufacturing device comprising:

a vacuum chamber;

a mechanical driver in the vacuum chamber that drives a semiconductor substrate holder;

a discharge port that introduces an inert gas into the vacuum chamber; and
a flow rate controller that controls the flow of inert gas through the discharge port.

Claim 8. (New) The device of claim 7, wherein the mechanical driver is adapted to drive the semiconductor substrate holder to translate, rotate and tilt.

Claim 9. (New) The device of claim 7, wherein the flow rate controller controls the flow of inert gas to provide a constant flow rate.

Claim 10. (New) The device of claim 7, further comprising an inspection part in the vacuum chamber.

Claim 11. (New) The device of claim 7, further comprising an exposure part in the vacuum chamber.

Claim 12. (New) The device of claim 7, wherein the discharge port is positioned in the vicinity of the semiconductor substrate holder.

Claim 13. (New) The device of claim 7, further comprising an exhaust port in the vacuum chamber.

Claim 14. (New) The device of claim 13, wherein the mechanical driver is positioned between the discharge port and the exhaust port.

Claim 15. (New) The device of claim 13, further comprising a vacuum pump connected to the exhaust port.

Claim 16. (New) The device of claim 15, wherein the vacuum pump has an evacuation rate of between about 300 Liters per second and 5,000 Liters per second.

Claim 17. (New) The device of claim 7, wherein the flow rate controller controls the flow of inert gas through the discharge port to be above about 0.5 cubic centimeters per minute.

Claim 18. (New) The device of claim 7, wherein the flow rate controller controls the flow of inert gas through the discharge port to be below about 20 cubic centimeters per minute.

Claim 19. (New) The device of claim 7, wherein the pressure within the vacuum chamber is above about 133×10^{-7} kiloPascals.

Claim 20. (New) The device of claim 7, wherein the pressure within the vacuum chamber is below about 133×10^{-4} kiloPascals.